

High Stability, Low Noise Vibration Rejecting Yaw Rate Gyroscope

Enhanced Product

ADXRS646-EP

FEATURES

12°/hr bias stability Z-axis (yaw rate) response 0.01°/√sec angle random walk High vibration rejection over wide frequency Measurement range extendable to a maximum of ±450°/sec 10,000 g powered shock survivability Ratiometric to referenced supply 6 V single-supply operation Self-test on digital command Ultrasmall and light (<0.15 cc, <0.5 gram) Temperature sensor output Complete rate gyroscope on a single chip RoHS compliant

ENHANCED PRODUCT FEATURES

Supports defense and aerospace applications (AQEC standard) Extended industrial temperature range (-55°C to +105°C) Controlled manufacturing baseline 1 assembly/test site 1 fabrication site Enhanced product change notification Qualification data available on request

APPLICATIONS

Industrial applications Severe mechanical environments Platform stabilization

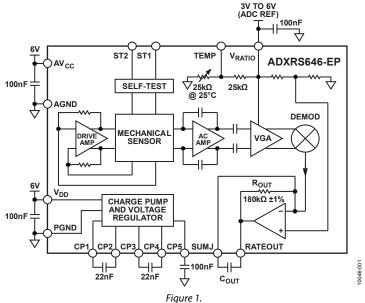
GENERAL DESCRIPTION

The ADXRS646-EP is a high performance angular rate sensor (gyroscope) that offers excellent vibration immunity. Bias stability is a widely recognized figure of merit for high performance gyroscopes, but in real-world applications, vibration sensitivity is often a more significant performance limitation and should be considered in gyroscope selection. The ADXRS646-EP offers superior vibration immunity and acceleration rejection as well as a low bias drift of 12°/hr (typical), enabling it to offer rate sensing in harsh environments where shock and vibration are present.

The ADXRS646-EP is manufactured using the Analog Devices, Inc., patented high volume BiMOS surface-micromachining process. An advanced, differential, quad sensor design provides the improved acceleration and vibration rejection. The output signal, RATEOUT, is a voltage proportional to angular rate about the axis normal to the top surface of the package. The measurement range is a minimum of $\pm 250^{\circ}$ /sec. The output is ratiometric with respect to a provided reference supply. Other external capacitors are required for operation.

A temperature output is provided for compensation techniques. Two digital self-test inputs electromechanically excite the sensor to test proper operation of both the sensor and the signal conditioning circuits.

The ADXRS646-EP is available in a 7 mm \times 7 mm \times 3 mm CBGA chip-scale package. Additional application and technical information can be found in the ADXRS646-EP data sheet.



FUNCTIONAL BLOCK DIAGRAM

Rev. 0

Document Feedback

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REVISION HISTORY

10/12—Revision 0: Initial Version

SPECIFICATIONS

All minimum and maximum specifications are guaranteed. Typical specifications are not guaranteed.

 $T_{A} = 25^{\circ}C, V_{S} = AV_{CC} = V_{DD} = 6 \text{ V}, V_{RATIO} = AV_{CC}, \text{ angular rate} = 0^{\circ}/\text{sec}, \text{ bandwidth} = 80 \text{ Hz} (C_{OUT} = 0.01 \text{ }\mu\text{F}), I_{OUT} = 100 \text{ }\mu\text{A}, \pm 1 \text{ }g, \text{ unless} = 100 \text{ }\mu\text{C}, \pm 1 \text{ }g, \text{ }$ otherwise noted.

Table 1.

Parameter	Test Conditions/Comments	Min	Тур	Max	Unit	
SENSITIVITY ¹	Clockwise rotation is positive output					
Measurement Range ² Full-scale range over specifications rang		±250	±300		°/sec	
Initial			9	9.5	mV/°/sec	
Temperature Drift ³	erature Drift ³		±3		%	
Nonlinearity			0.01		% of FS	
NULL ¹						
Null	-40°C to +105°C	2.7	3.0	3.3	V	
Temperature Drift ³			±3		°/sec	
Linear Acceleration Effect	Any axis		0.015		°/sec/g	
Vibration Rectification	25 <i>g</i> rms, 50 Hz to 5 kHz		0.0001		°/sec/g ²	
NOISE PERFORMANCE						
Rate Noise Density $T_A \le 25^{\circ}C$			0.01		°/sec/√Hz	
Rate Noise Density	T _A ≤ 105°C		0.015		°/sec/√Hz	
Resolution Floor $T_A = 25^{\circ}$ C, 1 minute to 1 hour in-run			12		°/hr	
FREQUENCY RESPONSE						
Bandwidth ⁴	±3 dB user adjustable up to specification		1000		Hz	
Sensor Resonant Frequency		15.5	17.5	20	kHz	
SELF-TEST ¹						
ST1 RATEOUT Response	ST1 pin from Logic 0 to Logic 1		-50		°/sec	
ST2 RATEOUT Response	ST2 pin from Logic 0 to Logic 1		50		°/sec	
ST1 to ST2 Mismatch ⁵		-5	±0.5	+5	%	
Logic 1 Input Voltage	ST1 pin or ST2 pin	4			V	
Logic 0 Input Voltage				2	V	
Input Impedance	ST1 pin or ST2 pin to common	40	50	100	kΩ	
TEMPERATURE SENSOR ¹						
V _{олт} at 25°С	$Load = 10 M\Omega$	2.8	2.9	3.0	V	
Scale Factor ⁶	25° C, V _{RATIO} = 6 V		10		mV/°C	
Load to V_s			25		kΩ	
Load to Common			25		kΩ	
TURN-ON TIME ⁶	Power on to $\pm 0.5^{\circ}$ /sec of final with CP5 = 100 nF			50	ms	
OUTPUT DRIVE CAPABILITY						
Current Drive	For rated specifications			200	μA	
Capacitive Load Drive				1000	pF	
POWER SUPPLY						
Operating Voltage (V_s)		5.75	6.00	6.25	v	
Quiescent Supply Current			4		mA	
TEMPERATURE RANGE						
Specified Performance		-55		+105	°C	

¹ Parameter is linearly ratiometric with V_{RATIO} . ² Measurement range is the maximum range possible, including output swing range, initial offset, sensitivity, offset drift, and sensitivity drift at 5 V supplies. ³ From +25°C to -40°C or +25°C to +105°C.

⁴ Adjusted by external capacitor, C_{0UT}. Reducing bandwidth below 0.01 Hz does not result in further noise improvement.
⁵ Self-test mismatch is described as (ST2 + ST1)/((ST2 - ST1)/2).

⁶ Based on characterization.

ABSOLUTE MAXIMUM RATINGS

Table 2.

Parameter	Rating
Acceleration (Any Axis, 0.5 ms)	
Unpowered	10,000 <i>g</i>
Powered	10,000 <i>g</i>
V _{DD} , AV _{CC}	–0.3 V to +6.6 V
Vratio	AVcc
ST1, ST2	AV _{CC}
Output Short-Circuit Duration (Any Pin to Common)	Indefinite
Operating Temperature Range	–65°C to +125°C
Storage Temperature Range	-65°C to +150°C

Stresses above those listed under the Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Drops onto hard surfaces can cause shocks of greater than 10,000 *g* and can exceed the absolute maximum rating of the device. Care should be exercised in handling to avoid damage.

RATE SENSITIVE AXIS

This is a Z-axis rate-sensing device (also called a yaw ratesensing device). It produces a positive going output voltage for clockwise rotation about the axis normal to the package top, that is, clockwise when looking down at the package lid.

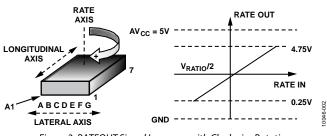


Figure 2. RATEOUT Signal Increases with Clockwise Rotation

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

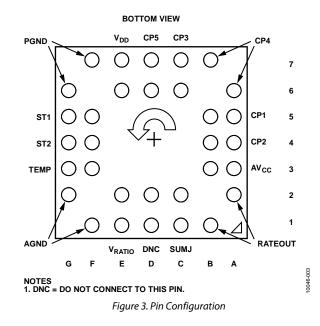


Table 3. Pin Function Descriptions

Pin No.	Mnemonic	Description	
6D, 7D	CP5	HV Filter Capacitor, 100nF (±5%).	
6A, 7B	CP4	Charge Pump Capacitor, 22 nF (±5%).	
6C, 7C	CP3	Charge Pump Capacitor, 22 nF (±5%).	
5A, 5B	CP1	Charge Pump Capacitor, 22 nF (±5%).	
4A, 4B	CP2	Charge Pump Capacitor, 22 nF (±5%).	
3A, 3B	AV _{cc}	Positive Analog Supply.	
1B, 2A	RATEOUT	Rate Signal Output.	
1C, 2C	SUMJ	Output Amp Summing Junction.	
1D, 2D	DNC	Do Not Connect to this Pin.	
1E, 2E	V _{RATIO}	Reference Supply for Ratiometric Output.	
1F, 2G	AGND	Analog Supply Return.	
3F, 3G	TEMP	Temperature Voltage Output.	
4F, 4G	ST2	Self-Test for Sensor 2.	
5F, 5G	ST1	Self-Test for Sensor 1.	
6G, 7F	PGND	Charge Pump Supply Return.	
6E, 7E	V _{DD}	Positive Charge Pump Supply.	

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TYPICAL PERFORMANCE CHARACTERISTICS

N > 1000 for all typical performance plots, unless otherwise noted.

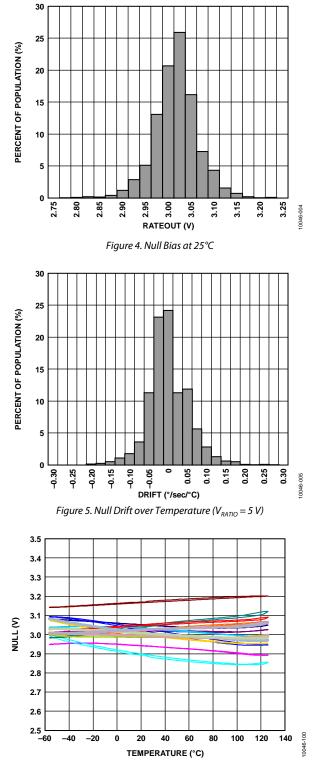
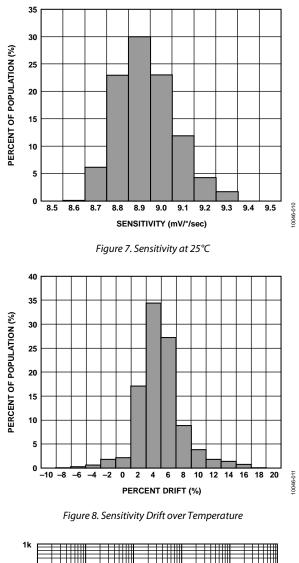


Figure 6. Null Output over Temperature, 16 Parts in Sockets ($V_{RATIO} = 5 V$)



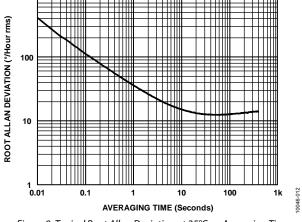


Figure 9. Typical Root Allan Deviation at 25°C vs. Averaging Time

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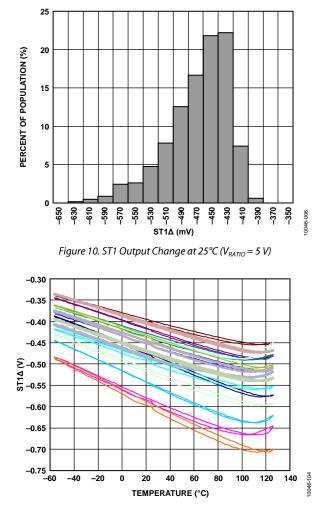


Figure 11. ST1 Output Change vs. Temperature, 16 Parts in Sockets

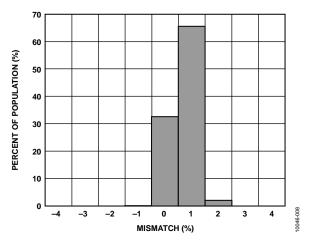
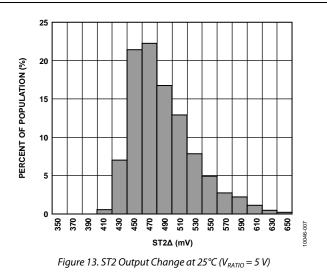


Figure 12. Self-Test Mismatch at 25°C ($V_{RATIO} = 5 V$)



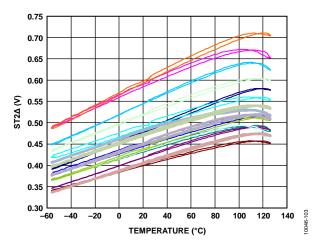


Figure 14. ST2 Output Change vs. Temperature, 16 Parts in Sockets

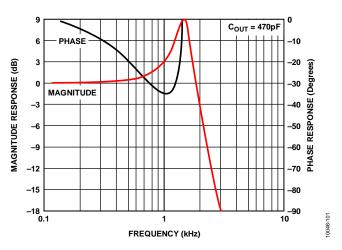


Figure 15. ADXRS646-EP Frequency Response with a 2.2 kHz Output Filter

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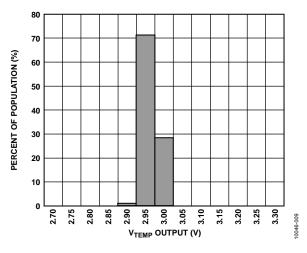
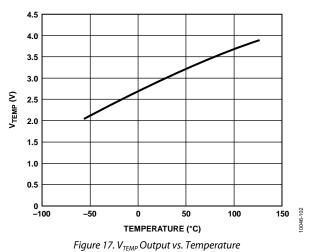


Figure 16. V_{TEMP} Output at 25°C ($V_{RATIO} = 5 V$)



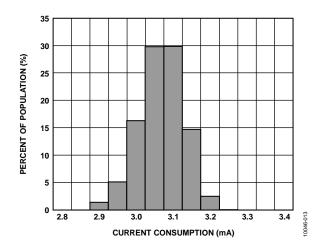
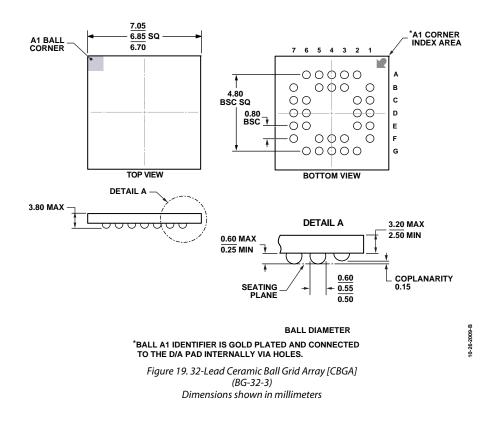


Figure 18. Current Consumption at 25°C ($V_{RATIO} = 5 V$)

OUTLINE DIMENSIONS



ORDERING GUIDE

Model ¹ Temperature Range Package Desc		Package Description	Package Option
ADXRS646TBGZ-EP	–55°C to +105°C	32-Lead Ceramic Ball Grid Array [CBGA]	BG-32-3
ADXRS646TBGZ-EP-RL	–55°C to +105°C	32-Lead Ceramic Ball Grid Array [CBGA]	BG-32-3

¹ Z = RoHS Compliant Part.

NOTES

NOTES

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NOTES

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